

SMD Type

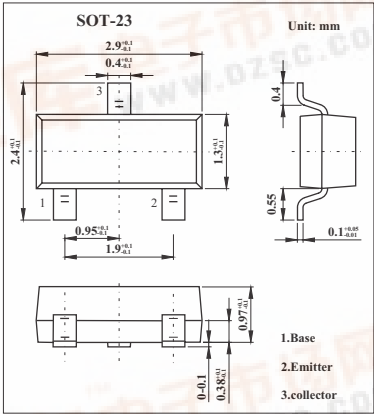
Transistors

NPN Transistors

KST8050S

■ Features

- Collector Current: Ic=0.5A



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	40	V
Collector-Emitter Voltage	Vceo	25	V
Emitter-Base Voltage	Vebo	5	V
Collector Current -Continuous	Ic	0.5	A
Collector Dissipation	Pc	0.3	W
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55 to 150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	Vcbo	Ic = 100 μA , IE = 0	40			V
Collector-emitter breakdown voltage	Vceo	Ic = 1mA , IB = 0	25			V
Emitter-base Breakdown voltage	Vebo	IE = 100 μA , Ic = 0	5			V
Collector-base cut-off current	Icbo	Vcb = 40 V , IE = 0			0.1	μ A
Collector-emitter cut-off current	Iceo	Vce = 20 V , IB = 0			0.1	μ A
Emitter-base cut-off current	Iebo	VEB = 5 V , Ic = 0			0.1	μ A
DC current gain	hFE	VCE = 1 V , Ic = 50 mA	120		350	
		VCE = 1 V , Ic = 500 mA	50			
Collector-emitter saturation voltage	VCE(sat)	Ic = 500 mA , IB = 50 mA			0.6	V
Base-emitter saturation voltage	VBE(sat)	Ic = 500 mA , IB = 50 mA			1.2	V
Transition frequency	fr	VCE = 6 V , Ic = 20 mA , f = 30 MHz	150			MHz

■ hFE Classification

Marking	J3Y	
Rank	L	H
hFE	120~200	200~350



KST8050S

■ Typical Characteristics

